

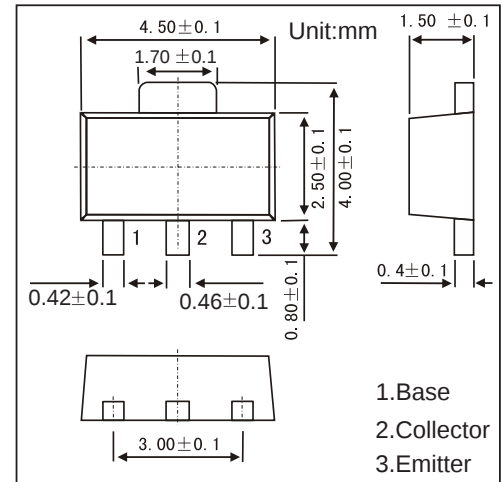
SOT-89 Plastic-Encapsulate Transistors

FEATURES

- Collector Current Capability $I_C=2A$
- Collector Emitter Voltage $V_{CEO}=32V$
- High-speed switching
- Complements to 2SB1188
- NPN Transistors

MECHANICAL DATA

- Case style:SOT-89molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	40	V
Collector - Emitter Voltage	V_{CEO}	32	
Emitter - Base Voltage	V_{EBO}	5	
Collector Current - Continuous	I_C	2	A
Collector Power Dissipation	P_C	0.5	W
Junction Temperature	T_J	150	°C
Storage Temperature range	T_{stg}	-55 to +150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = 100 \mu A, I_E = 0$	40			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = 1 mA, I_B = 0$	32			
Emitter - base breakdown voltage	V_{EBO}	$I_E = 100 \mu A, I_C = 0$	5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 20 V, I_E = 0$			1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 4 V, I_C = 0$			1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 2 A, I_B = 200 mA$			0.8	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 2 A, I_B = 200 mA$			1.2	
DC current gain	h_{FE}	$V_{CE} = 3 V, I_C = 500 mA$	82		390	
Collector output capacitance	C_{ob}	$V_{CB} = 10 V, I_E = 0, f = 1 MHz$		30		pF
Transition frequency	f_T	$V_{CE} = 5 V, I_E = 50 mA, f = 100 MHz$		100		MHz

RATINGS AND CHARACTERISTIC CURVES

